SUPPORT FOR THE AMENDMENT

Claims 3, 7, and 8 are currently amended.

Claims 17-21 are added.

Support for the amendment to claim 7 can be found in the specification at page 20, lines 10-15, as originally filed.

Claims 3 and 8 have been amended to remove multiple dependencies.

Support for claims 17-21 can be found in the specification at page 20, lines 16-19, page 21, lines 25-27, and page 29, lines 5-10 and 19-24, as originally filed.

No new matter has been added by these amendments.

Upon entry of this amendment, claims 1-21 will be active in this application.

It is noted that claims 1-6 and 8 have been withdrawn, in view of a Restriction Requirement.

It is also noted that the claims have been restricted to a single elected species. However,

Applicants request that the Examiner expand her search to include the non-elected species,

and rejoinder of the non-elected claims is also requested.

REQUEST FOR RECONSIDERATION

The rejection of claims 7, 9, and 17 under 35 U.S.C. § 102(b) as anticipated by U.S. Patent No. 6,383,240 to Nishimoto et al., and the rejection of claims 12-15 under 35 U.S.C. § 103(a) as obvious over Nishimoto et al. are traversed and obviated by amendments.

The reference does not describe or suggest the claimed process, which includes the incorporation of the abrasive grains and a hetercyclic compound.

In particular, the <u>Nishimoto et al</u>. merely describes an aqueous dispersion for chemical mechanical polishing (CMP) that includes abrasive particles, an amphipathic compound, and water. (See Abstract, and generally columns 2 through 5 of the reference).

By contrast, in the present invention, the most characterized feature resides in that the abrasive grains contain both of simple particles and specific composite particles composed of inorganic organic composite particles, as recited in claim 7. Specifically, when an aqueous dispersion for CMP which contains simple particles or inorganic particles as the abrasive grains without any composite particles is used, the number of scratches on the surface of the dielectrics of low dielectric constant is increased and peeling partially occurs. These results are evidenced by the Examples in the present specification, e.g., as shown in Comparative Examples 1 and 2 compared with Examples 1-5 in the Table 1 on page 45 of the present specification.

As currently amended, the aqueous dispersion for CMP according to the claimed invention contains a heterocyclic compound (claim 7 and 17-18), as well as an organic acid (claims 19-21), in which a superior effect is attained such that both copper films and barrier metal films can be polished with high efficiency, and a sufficiently planarized finished surface with high precision without overpolishing dielectrics can be obtained.

There is no suggestion or evidentiary support for such an effect in the <u>Nishimoto et al</u>. reference. As such, the claimed invention is novel and unobvious over the reference.

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Accordingly, withdrawal of the rejections is requested.

Applicants submit that new claims 17-21 are also novel and unobvious, since the reference does not describe or suggest the claimed method with these features.

Applicants submit that this application is now in condition for allowance and early notification of such is earnestly solicited.

Should the Examiner deem that any further action is necessary to place this application in even better form for allowance, the Examiner is encouraged to contact Applicants' undersigned representative at the below listed telephone number.

Respectfully submitted,

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